

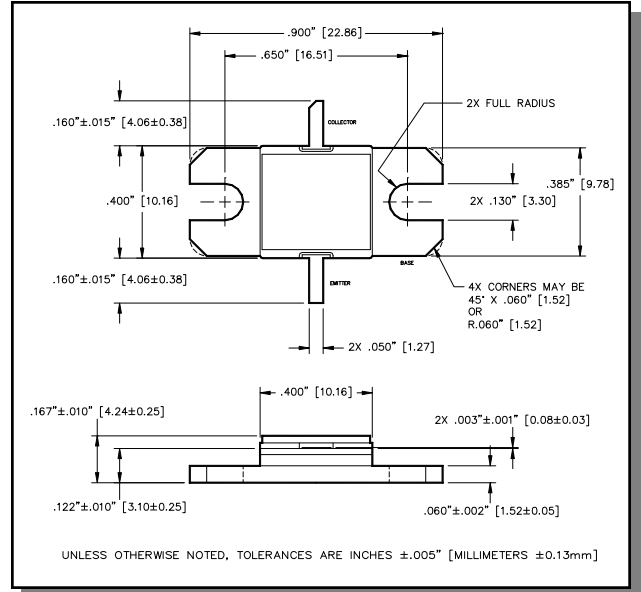
**Radar Pulsed Power Transistor**  
**20W, 2.9-3.1 GHz, 100µs Pulse, 10% Duty**

**M/A-COM Products**  
**Released, 10 Aug 07**

## Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

## Outline Drawing



## Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	65	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	$I_C$	1.85	A
Power Dissipation @ +25°C	$P_{TOT}$	115	W
Storage Temperature	$T_{STG}$	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

## Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient )

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$		$BV_{CES}$	65	-	V
Collector-Emitter Leakage Current	$V_{CE} = 40\text{V}$		$I_{CES}$	-	1.5	mA
Thermal Resistance	$V_{CC} = 36\text{V}$ , $P_{in} = 3.0\text{W}$	F = 2.9, 3.0, 3.1 GHz	$R_{TH(JC)}$	-	1.5	°C/W
Output Power	$V_{CC} = 36\text{V}$ , $P_{in} = 3.0\text{W}$	F = 2.9, 3.0, 3.1 GHz	$P_{OUT}$	20	-	W
Power Gain	$V_{CC} = 36\text{V}$ , $P_{in} = 3.0\text{W}$	F = 2.9, 3.0, 3.1 GHz	$G_P$	8.2	-	dB
Collector Efficiency	$V_{CC} = 36\text{V}$ , $P_{in} = 3.0\text{W}$	F = 2.9, 3.0, 3.1 GHz	$\eta_C$	45	-	%
Input Return Loss	$V_{CC} = 36\text{V}$ , $P_{in} = 3.0\text{W}$	F = 2.9, 3.0, 3.1 GHz	RL	-	-6	dB
Load Mismatch Tolerance	$V_{CC} = 36\text{V}$ , $P_{in} = 3.0\text{W}$	F = 2.9, 3.0, 3.1 GHz	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 36\text{V}$ , $P_{in} = 3.0\text{W}$	F = 2.9, 3.0, 3.1 GHz	VSWR-S	-	1.5:1	-

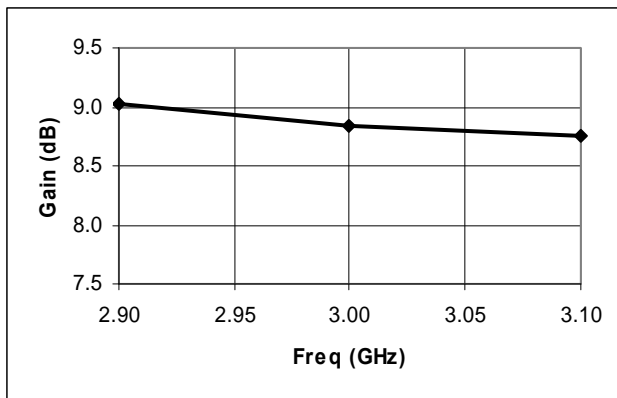
Radar Pulsed Power Transistor  
20W, 2.9-3.1 GHz, 100µs Pulse, 10% Duty

M/A-COM Products  
Released, 10 Aug 07

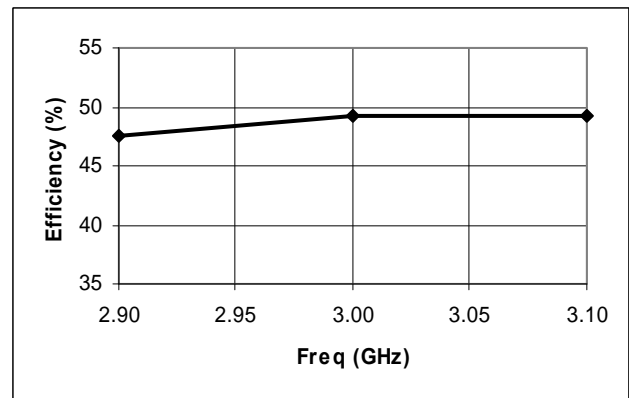
## Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
2.9	3.0	24.0	9.03	1.41	47.5	-19.1	S	P
3.0	3.0	23.0	8.85	1.30	49.2	-16.9	S	P
3.1	3.0	22.5	8.75	1.27	49.3	-19.4	S	P

## Gain vs. Frequency

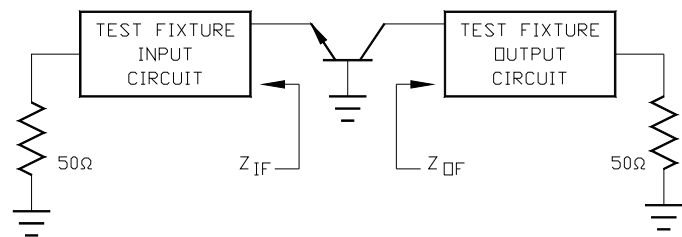


## Collector Efficiency vs. Frequency



## RF Test Fixture Impedance

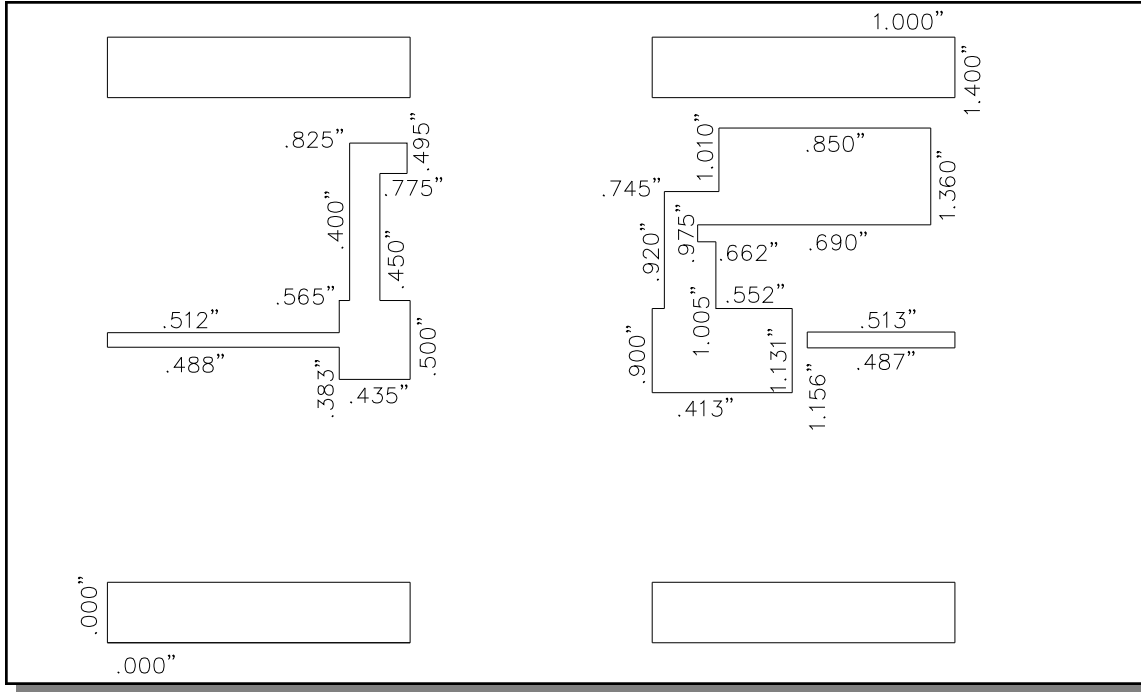
F (GHz)	Z <sub>IF</sub> (Ω)	Z <sub>OF</sub> (Ω)
2.9	33.0 - j17.8	13.3 - j8.3
3.0	30.0 - j19.0	12.0 - j7.9
3.1	27.0 - j19.4	10.9 - j7.4



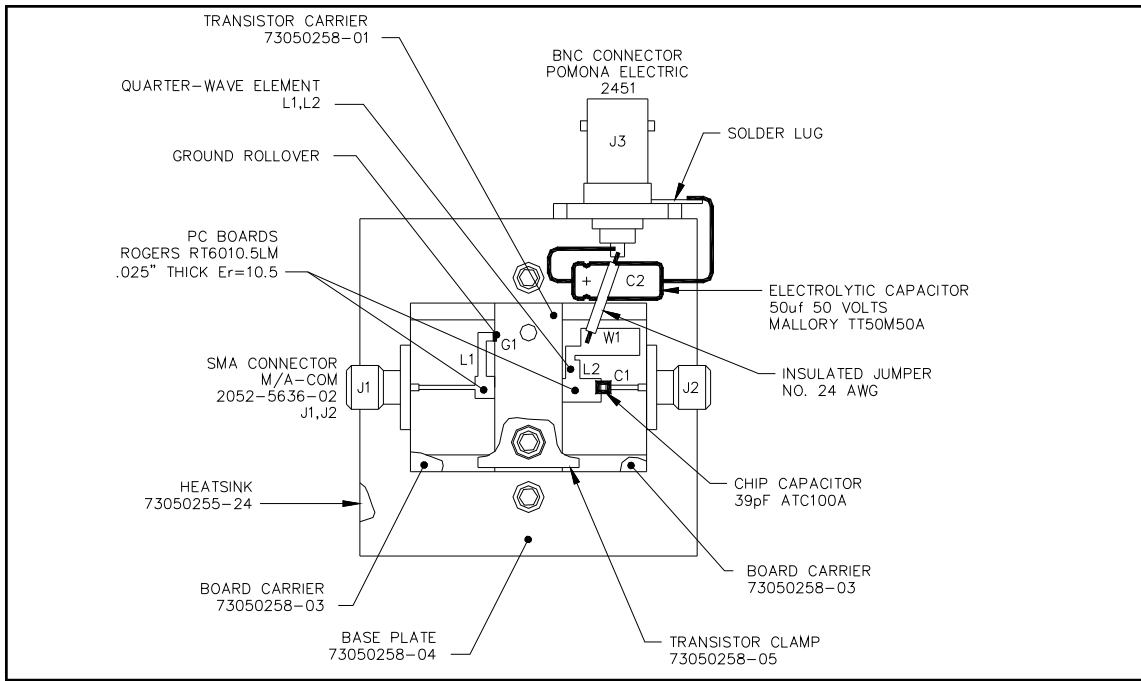
Radar Pulsed Power Transistor  
20W, 2.9-3.1 GHz, 100µs Pulse, 10% Duty

M/A-COM Products  
Released, 10 Aug 07

## Test Fixture Circuit Dimensions



## Test Fixture Assembly



**ADVANCED:** Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

**PRELIMINARY:** Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- **North America** Tel: 800.366.2266 / Fax: 978.366.2266
  - **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300
  - **Asia/Pacific** Tel: 81.44.844.8296 / Fax: 81.44.844.8298
- Visit [www.macomtech.com](http://www.macomtech.com) for additional data sheets and product information.

M/A-COM Technology Solutions Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.